

**Metric Prefixes**

peta	P	$10^{15}$	1 000 000 000 000 000
tera	T	$10^{12}$	1 000 000 000 000
giga	G	$10^9$	1 000 000 000
mega	M	$10^6$	1 000 000
kilo	k	$10^3$	1 000
hecto	h	$10^2$	100
deca	da	$10^1$	10
one		$10^0$	1
deci	d	$10^{-1}$	0.1
centi	c	$10^{-2}$	0.01
milli	m	$10^{-3}$	0.001
micro	$\mu$	$10^{-6}$	0.000 001
nano	n	$10^{-9}$	0.000 000 001
pico	p	$10^{-12}$	0.000 000 000 001
femto	f	$10^{-15}$	0.000 000 000 000 001

**De Morgan's Laws**

- $\overline{AB} = \overline{A} + \overline{B}$
- $\overline{A + B} = (\overline{A})(\overline{B})$

**Silicon**

- Si
- P-type:
  - \* doped with material to remove electrons (add electron holes), usually Boron (B), Aluminum (Al), or Gallium (Ga)
- N-type:
  - \* doped with material to add electrons, usually Antimony (Sb), Arsenic (As), or Phosphorous (P)
- Silicon dioxide:  $\text{SiO}_2$

**Transistors**

- pMOS:
  - \* has the bubble
  - \* on when input is 0, off when input is 1
- nMOS
  - \* no bubble
  - \* on when input is on, off when input is off

**Fabrication**

- n-well: use diffusion or ion implantation
- positive lithography: expose to UV where you want to remove material
- negative lithography: expose to UV where you want to keep material

**D Flip Flop vs Latch**

- latch is level triggered
- flip flop is edge triggered